

WHAT IS CLAIMED IS:

1. A local dry etching apparatus for removing unevenness on a surface of a semiconductor wafer by blowing a gas including an activated species produced by a plasma and injected from a nozzle locally to the surface of the semiconductor wafer supported on a wafer table concentrically therewith:

wherein said wafer table is provided with a supporting face in a circular shape and a radius larger than a radius of the semiconductor wafer supported by the wafer table.

2. The local dry etching apparatus according to Claim 1:

wherein a value produced by subtracting the radius of said semiconductor wafer from the radius of said wafer table is large by an amount of 10 percent through 40 percent with a half value width of an etching rate of said injected gas.

3. The local dry etching apparatus according to Claim 1:

wherein the radius of said wafer table is larger than the radius of said semiconductor wafer by 4 mm through 10 mm.

4. A local dry etching method for removing unevenness on a surface of a semiconductor wafer by blowing a gas including an activated species produced by a plasma and injected from a nozzle locally

to the surface of the semiconductor wafer supported on a wafer table concentrically therewith:

wherein the radius of said wafer table is made larger than the radius of the semiconductor wafer.

5. The local dry etching method according to Claim 4:

wherein a value produced by subtracting the radius of said semiconductor wafer from the radius of said wafer table is made large by an amount of 10 percent through 40 percent with a half value width of an etching rate of said injected gas as a reference.

6. The local dry etching method according to Claim 4:

wherein the radius of said wafer table is made larger than the radius of said semiconductor wafer by 4 mm through 10 mm.

7. A wafer table for a local dry etching apparatus for removing unevenness on a surface of a semiconductor wafer by blowing a gas including an activated species produced by a plasma and injected from a nozzle locally to the surface of the semiconductor wafer supported on a wafer table concentrically therewith:

wherein said wafer table is provided with a supporting face in a circular shape and a radius larger than a radius of the semiconductor wafer supported by the supporting face.

8. The wafer table according to Claim 7:

wherein the wafer table is provided with the radius in which a value produced by subtracting the radius of said semiconductor wafer from the radius of said wafer table is large by an amount of 10 percent through 40 percent with a half value width of an etching rate of said injected gas as a reference.

9. The wafer table according to Claim 7:

wherein the wafer table is provided with the radius larger than the radius of said semiconductor wafer by 4 mm through 10 mm.